

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09314 DT-01-89

Silicon Planar Type

Diode

1S2460~1S2462

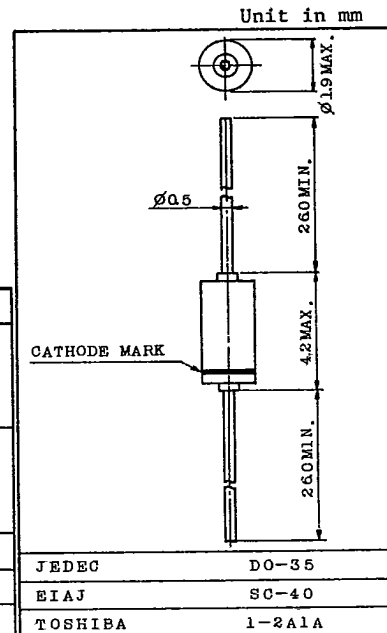
GENERAL PURPOSE RECTIFIER APPLICATIONS.

FEATURES:

- High Reverse Voltage : $V_R=200V$ (Min.) (1S2462)
- Low Forward Voltage : $V_F=1.0V$ (Max.)
- Hermetically Sealed Miniature Glass Package.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	1S2460	70	V
	1S2461	120	
	1S2462	220	
Reverse Voltage	1S2460	50	V
	1S2461	100	
	1S2462	200	
Maximum (Peak) Forward Current	I_{FM}	300	mA
Average Forward Current	I_O	100	mA
Surge Current (1 sec)	I_{FSM}	800	mA
Power Dissipation	P	250	mW
Junction Temperature	T_j	175	$^\circ C$
Storage Temperature Range	T_{stg}	-65 ~ 175	$^\circ C$

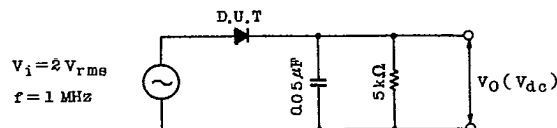


Weight : 0.14g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	$I_F=100mA$	-	0.9	1.0	V
Reverse Current	1S2460	$V_R=50V$	-	-	1.2	μA
	1S2461	$V_R=100V$				
	1S2462	$V_R=200V$				
Rectification Efficiency	η	$f=1MHz, V_i=2V_{rms}$ (Fig.)	35	-	-	%
Total Capacitance	CT	$V_R=0, f=1MHz$	-	5	10	pF

Fig. : TEST CIRCUIT



$$\eta = \frac{V_o(V_{dc})}{\sqrt{2} \times V_i(V_{rms})}$$

$$= 353 \times V_o(V_{dc})(\%)$$

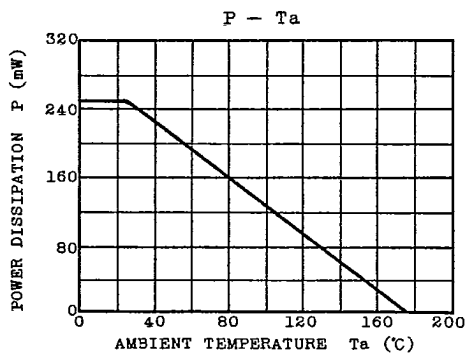
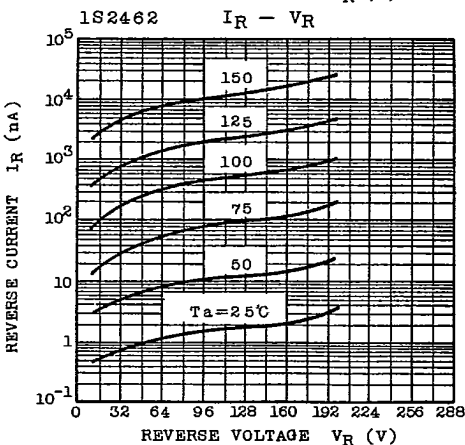
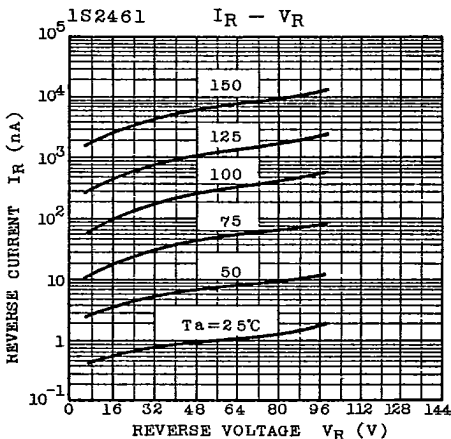
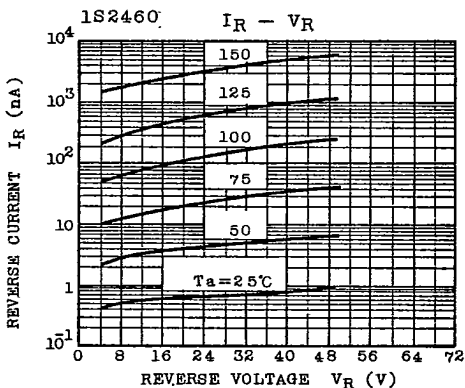
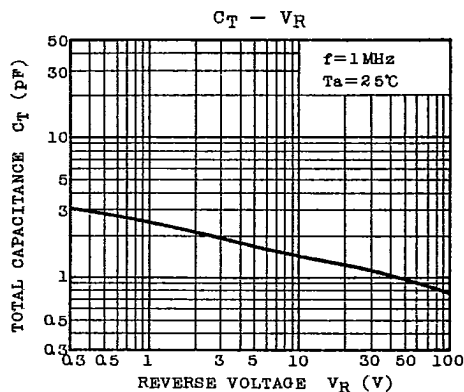
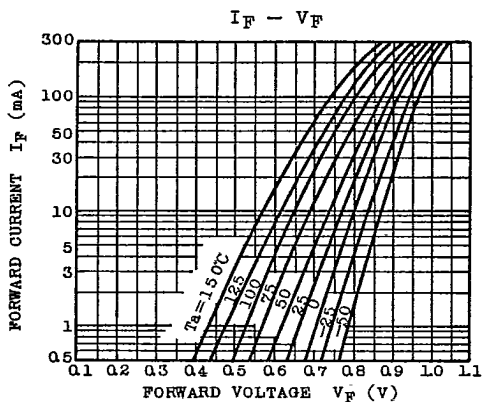
TOSHIBA CORPORATION

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